

AA028P2-00

Features

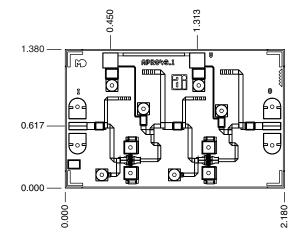
- Single Bias Supply Operation (6 V)
- 14 dB Typical Small Signal Gain
- 16 dBm Typical P_{1 dB} Output Power at 28 GHz
- 0.25 µm Ti/Pd/Au Gates
- 100% On-Wafer RF and DC Testing
- 100% Visual Inspection to MIL-STD-883 MT 2010

Description

Alpha's two-stage reactively-matched 27–31 GHz GaAs MMIC driver amplifier has typical small signal gain of 14 dB with a typical $P_{1 dB}$ of 16 dBm at 28 GHz. The chip uses Alpha's proven 0.25 μ m MESFET technology, and is based upon MBE layers and electron beam lithography for the highest uniformity and repeatability. The FETs employ surface passivation to ensure a rugged, reliable part with through-substrate via holes and gold-based backside metallization to facilitate a conductive epoxy die attach process. All chips are screened for gain, output power and S-parameters prior to shipment for guaranteed performance. Designed for 27–31 GHz LMDS and digital radio bands.

Electrical Specifications at $25^{\circ}C$ (V_{DS} = 6 V)

Chip Outline



Dimensions indicated in mm.

All DC (V) pads are 0.1 x 0.1 mm and RF In, Out pads are 0.07 mm wide. Chip thickness = 0.1 mm.

Absolute Maximum Ratings

Characteristic	Value	
Operating Temperature (T _C)	-55°C to +90°C	
Storage Temperature (T _{ST})	-65°C to +150°C	
Bias Voltage (V _D)	7 V _{DC}	
Power In (P _{IN})	16 dBm	
Junction Temperature (T _J)	175°C	

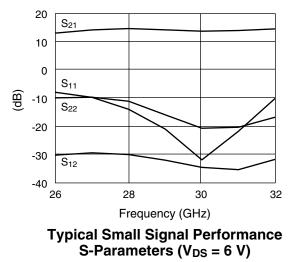
Parameter	Condition	Symbol	Min.	Typ. ²	Max.	Unit
Drain Current		I _{DS}		80	110	mA
Small Signal Gain	F = 27–31 GHz	G	12	14		dB
Input Return Loss	F = 27–31 GHz	RL		-11	-6	dB
Output Return Loss	F = 27–31 GHz	RLO		-12	-6	dB
Output Power at 1 dB Gain Compression	F = 28 GHz	P _{1 dB}	13	16		dBm
Saturated Output Power	F = 28 GHz	P _{SAT}	14	17		dBm
Thermal Resistance ¹		ΘJC		198		°C/W

1. Calculated value based on measurement of discrete FET.

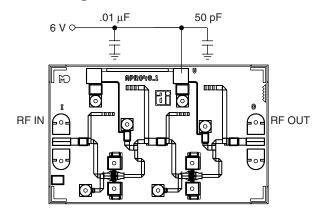
2. Typical represents the median parameter value across the specified

frequency range for the median chip.

Typical Performance Data



Bias Arrangement



For biasing on, adjust V_{DS} from zero to the desired value (6 V recommended). For biasing off, reverse the biasing on procedure.

Circuit Schematic

